# **Dynamic Characteristics**

## VRF152(MP)

Symbol	Parameter	Test Conditions	Min	Тур	Max	Unit
C <sub>ISS</sub>	Input Capacitance	V <sub>GS</sub> = 0V		383		
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> = 50V		215		pF
C <sub>rss</sub>	Reverse Transfer Capacitance	f = 1MHz		20		

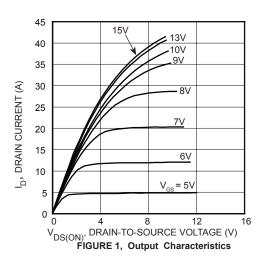
## **Functional Characteristics**

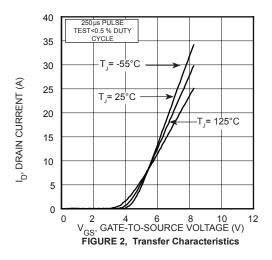
Symbol	Parameter	Min	Тур	Max	Unit
$G_{PS}$	$f_1 = 30MHz, f_2 = 30.001MHz, V_{DD} = 50V, I_{DQ} = 250mA, P_{out} = 150W_{PEP}^{-1}$	18	22		dB
$G_{PS}$	f = 175MHz, V <sub>DD</sub> = 50V, I <sub>DQ</sub> = 250mA, P <sub>out</sub> = 150W		14		uБ
$\eta_{\scriptscriptstyle D}$	$f_1 = 30MHz, f_2 = 30.001MHz, V_{DD} = 50V, I_{DQ} = 250mA, P_{out} = 150W_{PEP}^{-1}$		50		%
IMD <sub>(d3)</sub>	$f_1 = 30MHz, f_2 = 30.001MHz, V_{DD} = 50V, I_{DQ} = 250mA, P_{out} = 150W_{PEP}^{-1}$		-30		dBc
Ψ	$f = 30MHz$ , $V_{DD} = 50V$ , $I_{DQ} = 250mA$ , $P_{out} = 150W$ CW 70:1 VSWR - All Phase Angles, 0.2mSec X 20% Duty Factor	No Degradation in Output Power		Power	

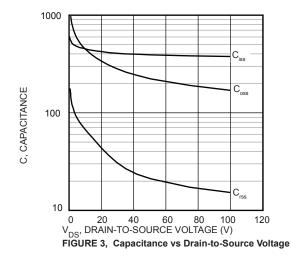
<sup>1.</sup> To MIL-STD-1311 Version A, test method 2204B, Two Tone, Reference Each Tone

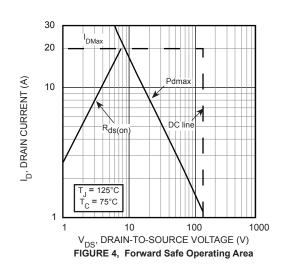
Microsemi reserves the right to change, without notice, the specifications and information contained herein.

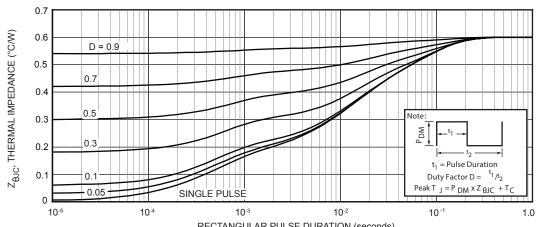
# **Typical Performance Curves**











RECTANGULAR PULSE DURATION (seconds)
Figure 5. Maximum Effective Transient Thermal Impedance Junction-to-Case vs Pulse Duration

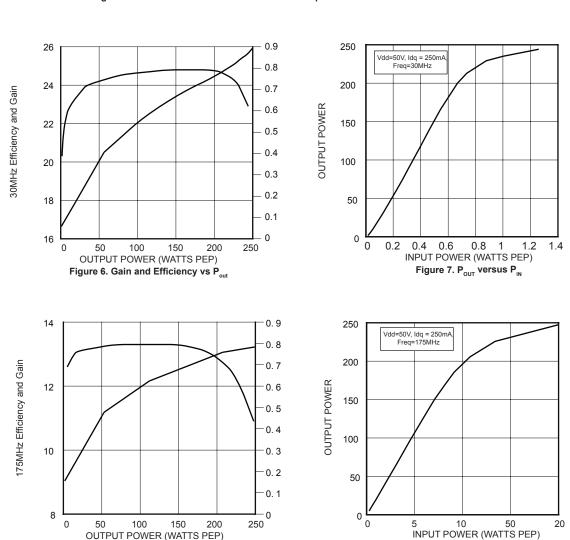
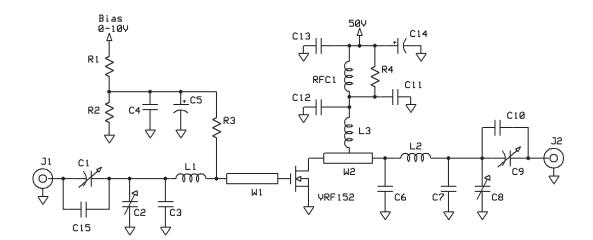


Figure 8. Gain and Efficiency vs Pout

Figure 9. P<sub>OUT</sub> versus P<sub>IN</sub>

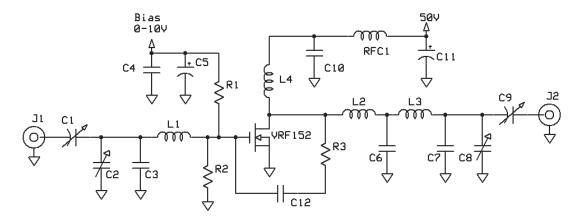
#### 30 MHz test Circuit



C1,2,8,9 - ARCO 463 20-180pF
C3,7 - 120 pF ATC 100B
C4,11-13 - 0.1uF 100V SMT
C5 - 1 uF 15WV tant
C6, C15 - 47pF ATC 100B
C10 - 150pF ATC 100B
C14 - 15uF 100V Elect
W1 W2 - printed line 0.23"x 0.7"

L1 - 4t #20 ga .25"d x .16"L ~120nH L2 - 5t #14 ga .312" dia x .45" ~135nH L3 -7 turns #16 ga 5/16" [D tight. ~250nH R1 R2 - 2.2k ohm 1/4W R3 - 22 ohm 1W SMT R4 - 2.2 ohm 2W RFC1 Fair-Rite 2961666631 (VK200-4B) PCB = FR-4 fiberglass-epoxy er = 4.6

## 175 MHz test Circuit



C1 C2 C8 - ARCO 463

C3 C7 - 25 pF ATC 100B

C4 C10 C12 - 0.1uF 100Y SMT

C5 - 1 uF 15WY tant

C6 - 250 pF ATC 100B

C9 - ARCO 462

C11 - 15uF 100Y Elect

L1 - 3/4" #18 ga into Hairpin

L2 - printed line 0.2"W x 0.5" L

L3 - 1" #16 ga into Hairpin

L4 -2 turns #16 ga. 5/16" ID

R1 R2 - 150 ohm 1W

R3 - 470 ohm 3W, Panasonic ECG

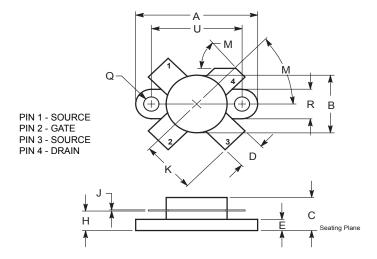
RFC1 Fair-Rite 2961666631 (VK200-4B)

Adding MP at the end of P/N specifies a matched pair where  $V_{\text{GS(TH)}}$  is matched between the two parts.  $V_{\text{TH}}$  values are marked on the devices per the following table.

Code	Vth Range	Code 2	Vth Range
А	2.900 - 2.975	М	3.650 - 3.725
В	2.975 - 3.050	N	3.725 - 3.800
С	3.050 - 3.125	Р	3.800 - 3.875
D	3.125 - 3.200	R	3.875 - 3.950
Е	3.200 - 3.275	S	3.950 - 4.025
F	3.275 - 3.350	Т	4.025 - 4.100
G	3.350 - 3.425	W	4.100 - 4.175
Н	3.425 - 3.500	Х	4.175 - 4.250
J	3.500 - 3.575	Υ	4.250 - 4.325
K	3.575 - 3.650	Z	4.325 - 4.400

 $<sup>{</sup>m V}_{_{
m TH}}$  values are based on Microsemi measurements at datasheet conditions with an accuracy of 1.0%.

# .5" SOE Package Outline All Dimensions are ± .005



DIM	INCHES		MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
А	0.096	0.990	24.39	25.14	
В	0.465	0.510	11.82	12.95	
С	0.229	0.275	5.82	6.98	
D	0.216	0.235	5.49	5.96	
Е	0.084	0.110	2.14	2.79	
Н	0.144	0.178	3.66	4.52	
J	0.003	0.007	0.08	0.17	
K	0.435		11.0		
М	45° NOM		45° NOM		
Q	0.115	0.130	2.93	3.30	
R	0.246	0.255	6.25	6.47	
U	0.720	0.730	18.29	18.54	

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